## GD10MPS17H 1700V 10A SiC Schottky MPS™ Diode

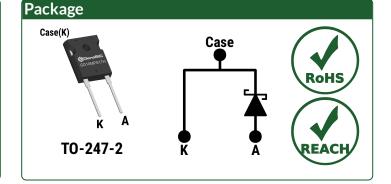
Silicon Carbide Schottky Diode



V <sub>RRM</sub> =	1700 V
I <sub>F(Tc</sub> = 160°C) =	10 A
Qc =	83 nC

#### Features

- Gen4 Thin Chip Technology for Low V<sub>F</sub>
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Q<sub>C</sub>/I<sub>F</sub>
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V<sub>F</sub>
- Low V<sub>F</sub> for High Temperature Operation



### Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Improved System Efficiency

#### Applications

- EV Fast Chargers
- Solar Inverters
- Anti-Parallel / Free-Wheeling Diode
- Motor Drives
- High Frequency Rectifiers
- Switched Mode Power Supply (SMPS)
- Induction Heating and Welding
- Pulsed Power

### Absolute Maximum Ratings (At Tc = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>		1700	V	
		T <sub>C</sub> = 100°C, D = 1	26		
Continuous Forward Current	lF	I <sub>F</sub> T <sub>C</sub> = 135°C, D = 1		Α	Fig. 4
		T <sub>C</sub> = 160°C, D = 1	10		
Non-Repetitive Peak Forward Surge Current, Half Sine Wave	Iŗ,sm	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 ms	100 A		
		T <sub>C</sub> = 150°C, t <sub>P</sub> = 10 ms	80	А	
Repetitive Peak Forward Surge Current, Half Sine Wave		T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 ms	60	Α	
	I <sub>F,RM</sub>	T <sub>C</sub> = 150°C, t <sub>P</sub> = 10 ms	42	A	
Non-Repetitive Peak Forward Surge Current	I <sub>F,MAX</sub>	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 μs	500	Α	
i <sup>2</sup> t Value	∫i²dt	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 ms	50	A <sup>2</sup> s	
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	L = 4 mH, I <sub>AS</sub> = 10 A	200	mJ	
Diode Ruggedness	dV/dt	V <sub>R</sub> = 0 ~ 1360 V	200	V/ns	
Power Dissipation	Ртот	T <sub>C</sub> = 25°C	218	W	Fig. 3
Operating and Storage Temperature	Tj, Tstg		-55 to 175	°C	



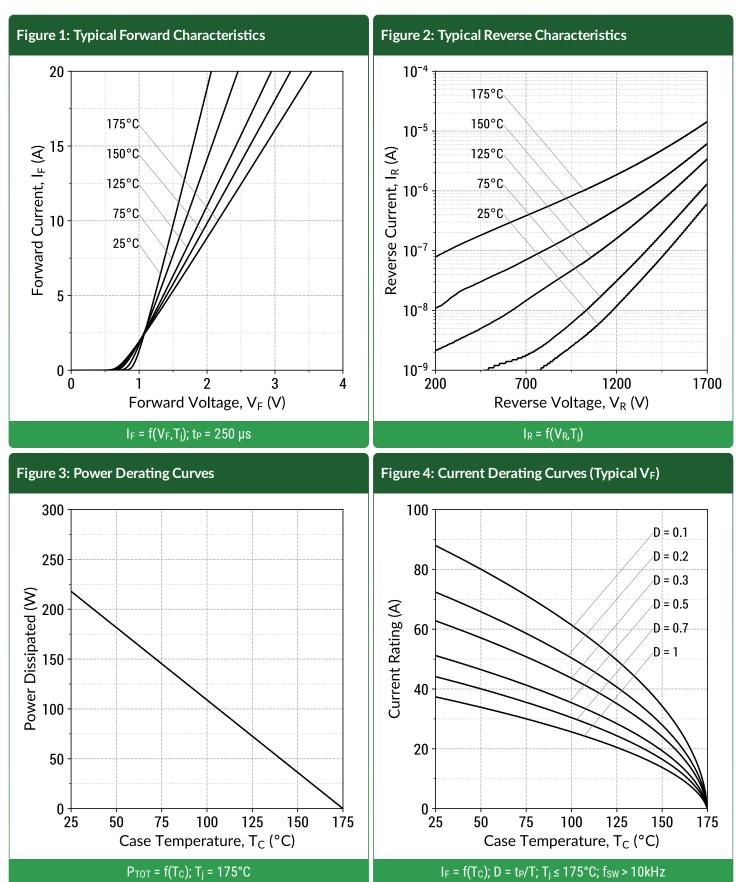
## **Electrical Characteristics**

Parameter	Symbol	Conditions -		Values			Unit	Note
	Symbol			Min.	Тур.	Max.	UIIIL	Note
Diada Farward Valtaga	VF	I <sub>F</sub> = 10 A, T <sub>j</sub> = 25°C			1.5	1.8	V	Fig. 1
Diode Forward Voltage	۷F	I <sub>F</sub> = 10 A, T <sub>j</sub> = 175°C			2.1			
Reverse Current	 	V <sub>R</sub> = 1700 V, T <sub>j</sub> = 25°C			1	20		Fig. 2
	IR	V <sub>R</sub> = 1700 V, T <sub>j</sub> = 175°C			7		μA	
Total Capacitive Charge	Qc	V <sub>R</sub> = 600 V			56		nC	Fig. 7
	QC	I <sub>F</sub> ≤ I <sub>F,MAX</sub>	V <sub>R</sub> = 1200 V		83		ПС	FIY. 7
Switching Time	+-	dl <sub>F</sub> /dt = 200 A/µs	V <sub>R</sub> = 600 V		< 10		<b>no</b>	
	ts		V <sub>R</sub> = 1200 V		< 10		ns	
Total Capacitance	0	V <sub>R</sub> = 1 V, f = 1MHz			721		<b>"</b> Г	Fig. 6
	С	V <sub>R</sub> = 1200 V, f = 1MHz			40		pF	

### Thermal/Package Characteristics

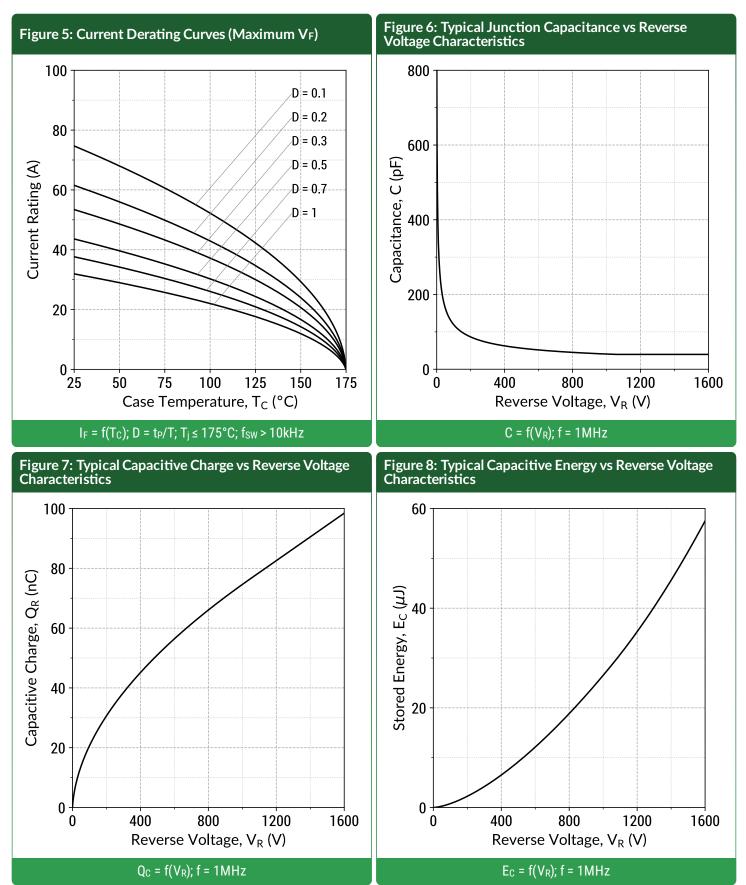
Parameter	Symbol	Conditions	Values			11	Note
			Min.	Тур.	Max.	<b>Unit</b>	Note
Thermal Resistance, Junction - Case	RthJC			0.69		°C/W	Fig. 9
Weight	WT			6.0		g	
Mounting Torque	Тм	Screws to Heatsink			1.1	Nm	





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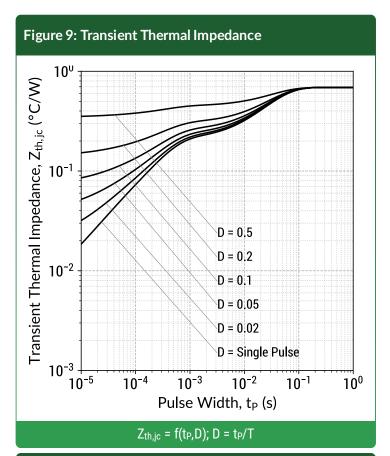


Figure 10: Forward Curve Model

 $I_F = f(V_F, T_j)$ 

### Forward Curve Model Equation:

 $I_{F} = (V_{F} - V_{BI})/R_{DIFF} (A)$ 

Built-In Voltage (V<sub>BI</sub>):

 $V_{BI}(T_j) = m \times T_j + n (V)$ m = -0.00126 (V/°C)

n = 0.997 (V)

Differential Resistance (RDIFF):

 $\begin{aligned} & \mathsf{R}_{\mathsf{DIFF}}(\mathsf{T}_j) = \mathbf{a} \times \mathsf{T}_j^2 + \mathbf{b} \times \mathsf{T}_j + \mathbf{c} \ (\Omega) \\ & \mathbf{a} = 1.02\text{e-}06 \ (\Omega/^\circ\text{C}^2) \\ & \mathbf{b} = 0.000352 \ (\Omega/^\circ\text{C}) \\ & \mathbf{c} = 0.0456 \ (\Omega) \end{aligned}$ 

Forward Power Loss Equation:

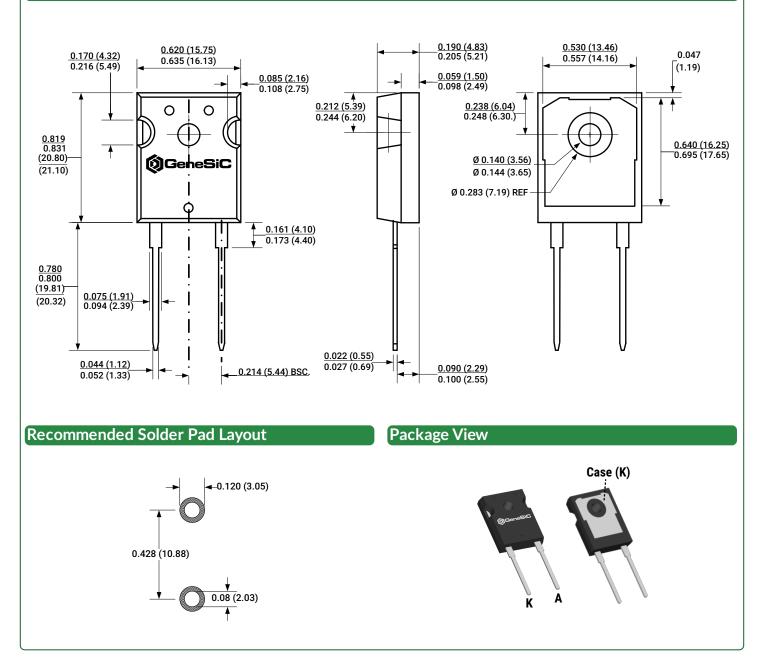
 $P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$ 





### Package Dimensions

### TO-247-2 Package Outline



#### NOTE

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

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### Compliance

#### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

#### **REACH Compliance**

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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### **Related Links**

- PLECS Models: https://www.genesicsemi.com/sic-schottky-mps/GD10MPS17H/GD10MPS17H\_PLECS.zip
- CAD Models: https://www.genesicsemi.com/sic-schottky-mps/GD10MPS17H/GD10MPS17H\_3D.zip
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#### **Revision History**

- Rev 21/Jun: Updated with most recent test data
- Supersedes: Rev 20/Jul



## www.genesicsemi.com/sic-schottky-mps/



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